Revision. 3

MOS FET

MTM981400BBF

Panasonic

MTM981400BBF

Silicon P-channel MOSFET

For switching

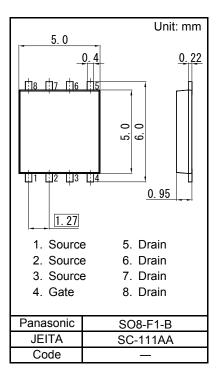
■ Features

- Low drain-source On-state Resistance RDS(on) typ = $28 \text{ m}\Omega$ (VGS = -4.5 V)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol BA

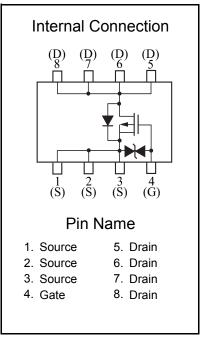
■ Packaging

Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard)



| Parameter | Symbol | Rating | Unit |
|-------------------------------|--------|-------------|------|
| Drain-source Voltage | VDS | -40 | V |
| Gate-source Voltage | VGS | ±20 | V |
| Drain Current | ID | -7.0 | Α |
| Drain Current (Pulsed) | IDp | -28 | Α |
| Total Power dissipation *1 | PD | 2 | W |
| Channel Temperature | Tch | 150 | °C |
| Operating Ambient Temperature | Topr | -40 to +85 | °C |
| Storage Temperature Range | Tstg | -55 to +150 | °C |

Note: *1 Measuring on ceramic board at 50 mm \times 50 mm \times 1.0 mm.



Doc No. TT4-EA-10096 Revision. 3

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■ Electrical Characteristics Ta = 25°C ± 3°C

Static Characteristics

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|-------------------------------------|----------|-----------------------------------|-----|-------|------|------|
| Drain-source Breakdown Voltage | VDSS | ID = -1 mA, VGS = 0 V | -40 | | | V |
| Zero Gate Voltage Drain Current | IDSS | VDS = -40 V, VGS = 0 V | | | -10 | μΑ |
| Gate-source Leakage Current | IGSS | VGS = ±16 V, VDS = 0 V | | | ±10 | μΑ |
| Gate-source threshold Voltage | Vth | ID = -1.0 mA, VDS = -10.0 V | -1 | | -2.5 | V |
| Drain-source On-state Resistance *1 | RDS(on)1 | ID = -7.0 A, VGS = -10 V | | 19 | 25 | mΩ |
| | RDS(on)2 | ID = -3.5 A, VGS = -4.5 V | | 28 | 45 | |
| Forward transfer admittance *1 | Yfs | ID = -7.0 A, VDS = -10 V | 10 | | | S |
| Input Capacitance | Ciss | | | 2 700 | | |
| Output Capacitance | Coss | VDS = -10 V, VGS = 0 V, f = 1 MH; | | 190 | | pF |
| Reverse Transfer Capacitance | Crss | | | 175 | | |
| Turn-on Delay Time *1,*2 | td(on) | VDD = -25 V, VGS = 0 V to -10 V | | 18 | | ns |
| Rise Time *1,*2 | tr | ID = -3.5 A | | 15 | | |
| Turn-off Delay Time *1,*2 | td(off) | VDD = -25 V, VGS = -10 V to 0 V | | 230 | | ns |
| Fall Time *1,*2 | tf | ID = -3.5 A | | 70 | | |

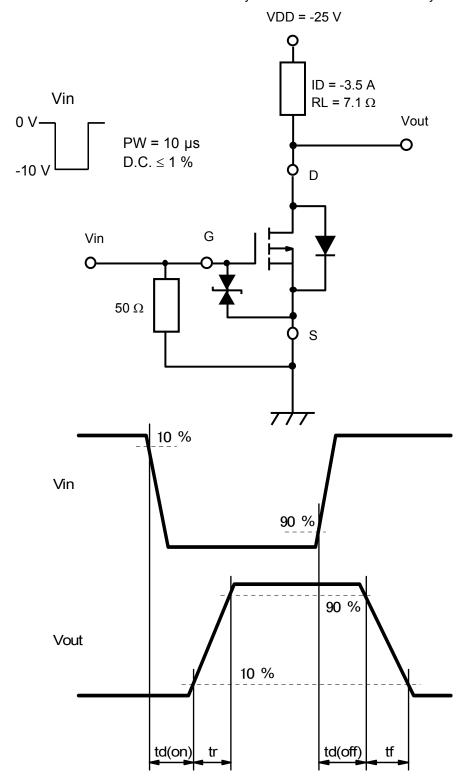
Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

Established: 2007-11-08 : 2013-10-15 Revised

^{2. *1} Pulse test

^{*2} Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



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Technical Data (reference)

ID - VDS -2.5 -10.0 V -2 Drain Current ID (A) -1.5 -1 -0.5 2.0 V 0 -0.04 -0.06 -0.08 -0.1 0 -0.02 Drain-source Voltage VDS (V)

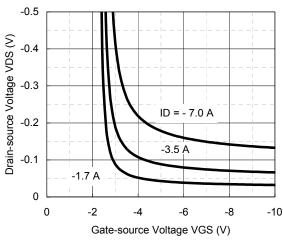
-3 Ta = 85 °C Ta = 85 °C -40 °C 0 -2.5 -1 -1.5 -2 -2.5

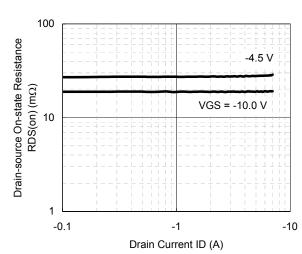
ID - VGS





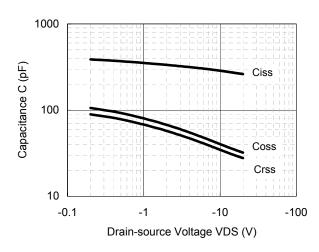
Gate-source voltage VGS (V)

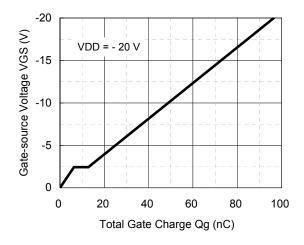




Capacitance - VDS

Dynamic Input/Output Characteristics

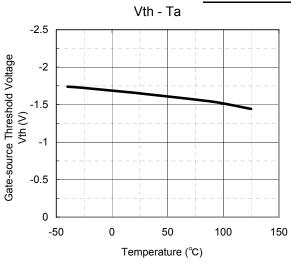


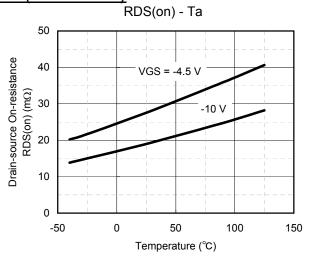


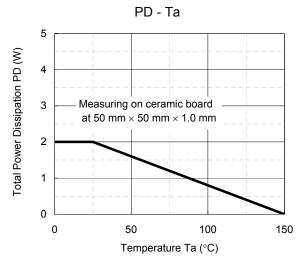
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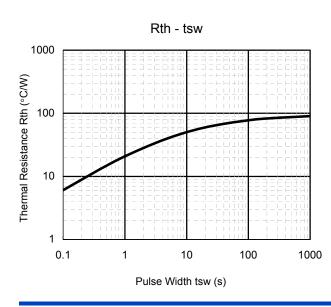
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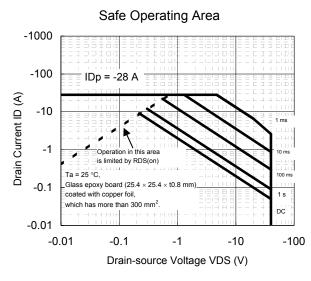
Technical Data (reference)











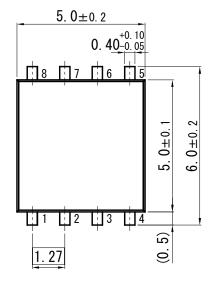
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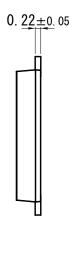
MOS FET

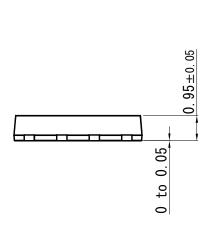
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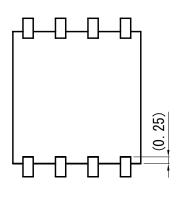
SO8-F1-B

Unit: mm

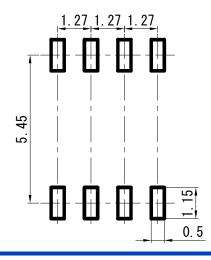








■ Land Pattern (Reference) (Unit: mm)



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